19-0810; Rev 0; 4/07

Overvoltage Protectors with External pFET

General Description

The MAX4923–MAX4926 overvoltage protection (OVP) controllers protect low-voltage systems against high-voltage faults of up to +28V with an appropriate external pFET. When the input voltage exceeds the overvoltage lockout (OVLO) threshold, or falls below the undervoltage lockout (UVLO) threshold, these devices turn off the pFET to prevent damage to protected components and issue a flag to notify the processor of a fault condition.

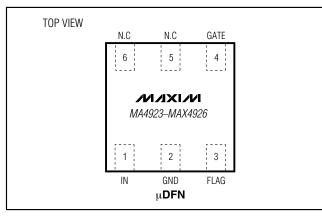
The typical overvoltage trip level is set to 7.18V (MAX4923), 6.16V (MAX4924), 5.65V (MAX4925), and 4.46V (MAX4926). The undervoltage trip level is set to 2.44V (typ) for all devices.

The input (IN) is ESD protected to ± 15 kV HBM when bypassed to ground with a 1µF ceramic capacitor. All devices are offered in a small, 6-pin (1.5mm x 1.0mm) µDFN package and are specified over the extended -40°C to +85°C temperature range.

> Cell Phones Digital Still Cameras PDAs and Palmtop Devices MP3 Players

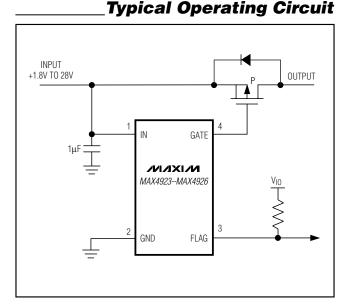
_Pin Configuration

Applications



_Features

- ♦ Overvoltage Protection Up to +28V
- Preset 7.18V, 6.16V, 5.65V, and 4.46V Typical Overvoltage Trip Levels
- Preset 2.44V Typical Undervoltage Trip Level
- ♦ ±2.5% Accurate Overvoltage/Undervoltage Trip Levels
- ◆ Low 13µA (typ) Supply Current
- Drives External pFET
- ♦ 20ms Adapter Debounce Time
- ♦ Fault Flag Indicator
- ♦ 6-Pin (1.5mm x 1.0mm) µDFN Package



Ordering Information/Selector Guide

PART	PIN-PACKAGE	OVLO (V)	UVLO (V)	TOP MARK	PKG CODE
MAX4923ELT+*	6 µDFN	7.18	2.44	LB	L611-1
MAX4924ELT+	6 µDFN	6.16	2.44	LC	L611-1
MAX4925ELT+	6 µDFN	5.65	2.44	LD	L611-1
MAX4926ELT+	6 µDFN	4.46	2.44	LE	L611-1

Note: All devices are specified over the -40°C to +85°C operating temperature range.

+Denotes lead-free package.

*Future Product—contact factory for availability.

_ Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim/Dallas Direct! at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

IN, GATE to GND	0.3V to +30V
FLAG to GND	0.3V to +6V
Continuous Power Dissipation ($T_A = +70^{\circ}C$)	
6-µDFN (derate 2.1mW/°C above 70°C)	168mW

Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(V_{IN} = +5V for MAX4923/MAX4924/MAX4925, V_{IN} = +4V for MAX4926, C_{GATE} = 500pF to IN, T_A = -40°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.) (Note 1)

PARAMETER	PARAMETER SYMBOL CONDITIONS		MIN	ТҮР	MAX	UNITS		
Input Voltage Range	VIN			1.8		28.0	V	
Overvoltage Lockout Level			MAX4923	7.00	7.18	7.36	V	
	OVLO	V _{IN} rising	MAX4924	6.00	6.16	6.31		
			MAX4925	5.50	5.65	5.79		
			MAX4926	4.35	4.46	4.57		
		MAX4923	·		65			
		MAX4924			55		<u>, /</u>	
Overvoltage Lockout Hysteresis		MAX4925			50		mV	
		MAX4926			40			
Undervoltage Lockout Level	UVLO	V _{IN} falling		2.378	2.439	2.500	V	
Undervoltage Lockout Hysteresis					20		mV	
		MAX4923/MAX4924/MAX4925			14	25	μA	
IN Supply Current	lin	MAX4926		Ì	13	23		
GATE Voltage High	V _{OH}	$V_{IN} \ge 8V$, $I_{SOURCE} = 0.1mA$		V _{IN} - 0.2			V	
GATE Pulldown Current	IPD	VGATE = VIN		6.5	12		mA	
FLAG Low Voltage	Vol	ISINK = 1mA				0.4	V	
FLAG Leakage Current	ILKG	V _{FLAG} = 5.5V		-1		+1	μA	
TIMING CHARACTERISTICS								
Debounce Time	t _{DEB}	V _{UVLO} < V _{IN} < V _{OVLO} , time for GATE to go low (Figure 1)		10	20	34	ms	
Gate Turn-on Time	tgon	V _{GATE} = 5V to 0.5V (MAX4923/MAX4924/MAX4925) or V _{GATE} = 4V to 0.5V (MAX4926) (Figure 1)			0.6		μs	
Gate Turn-Off Time	tgoff	V_{IN} rising at 1V/µs from 5V to 8V (MAX4923/MAX4924/MAX4925) or from 4V to 7V (MAX4926) to V _{GATE} = V _{IN} -0.5V (Figure 1)			5	20	μs	
Flag Assertion Delay	^t FLAG	V _{IN} rising at 1V μ (MAX4923/MAX4 to 7V (MAX4926) R _{FLAG} = 10kΩ to		4.5		μs		

Note 1: All devices are 100% tested at +25°C. Electrical limits across the full temperature range are guaranteed by design and characterization.

Typical Operating Characteristics

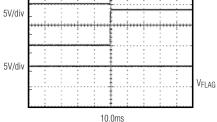
 $(V_{IN} = +5V \text{ for MAX4923/MAX4924/MAX4925}, V_{IN} = +4V \text{ for MAX4926} (pFET = Si6991DQ), T_A = +25^{\circ}C, unless otherwise noted.)$

GATE-OUTPUT LOW VOLTAGE GATE VOLTAGE vs. INPUT VOLTAGE vs. GATE SINK CURRENT **SUPPLY CURRENT vs. INPUT VOLTAGE** 250 100 10 MAX4925 GATE OUTPUT LOW VOLTAGE (mV) 80 8 200 SUPPLY CURRENT (MA) $V_{CC} = +2.5V$ MAX4925 GATE VOLTAGE (V) 150 60 6 $V_{CC} = +3.3V$ 40 100 4 MAX4926 20 50 2 $V_{CC} = +5.5V$ 0 0 0 1000 0 4 8 16 20 24 28 2 4 6 8 0 200 400 600 12 800 INPUT VOLTAGE (V) INPUT VOLTAGE (V) GATE SINK CURRENT (µA) **SUPPLY CURRENT vs. TEMPERATURE POWER-UP RESPONSE POWER-UP RESPONSE** MAX4923 toc06 VIN 15 MAX4926 5V/div $V_{CC} = +4V$ 5V/div VIN 14 SUPPLY CURRENT (MA) VOUT 5V/div 13 5V/div 1A/div VGATE I_{IN} 12 5V/div 5V/div 11 VFLAG VFLAG 10 -40 -15 10 35 60 85 20.0 ms 10.0ms TEMPERATURE (°C) **POWER-UP OVERVOLTAGE RESPONSE OVERVOLTAGE RESPONSE** 5V/div VIN VIN 5V/div 5V/div VGATE VGATE

10mA/div IGATE 5V/div VFLAG

20.0µs



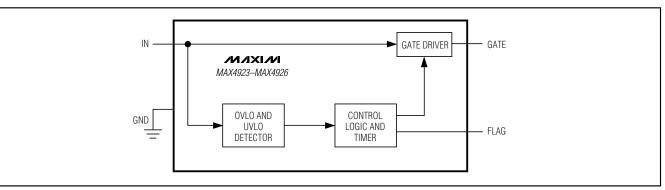


M/IXI/M

Pin Description

PIN	NAME	FUNCTION				
1	IN	Voltage Input. IN is both the power-supply input and the overvoltage/undervoltage sense input. Bypass IN to GND with a 1μ F ceramic capacitor as close as possible to the device to enable ± 15 kV (HBM) ESD protection on IN.				
2	GND	Ground				
3	FLAG	Fault Indication Open-Drain Output. FLAG deasserts high during undervoltage and overvoltage lockout conditions. FLAG asserts low during normal operation.				
4	GATE	pFET Gate Drive Output. GATE is driven high during a fault condition to turn off the external pFET. When $V_{UVLO} < V_{IN} < V_{OVLO}$, GATE is driven low and the external pFET is turned on.				
5, 6	N.C.	No Connection. Not internally connected. Leave N.C. unconnected.				

Functional Diagram



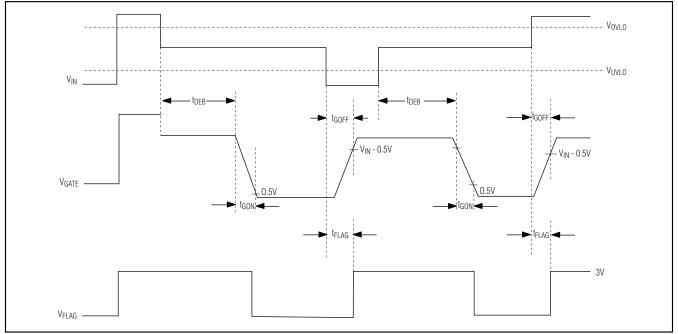


Figure 1. Timing Diagram

MAX4923-MAX4926

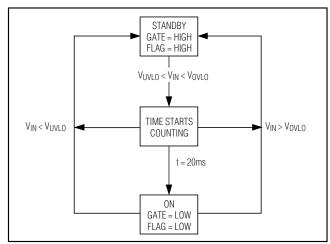


Figure 2. State Machine

Detailed Description

The MAX4923–MAX4926 overvoltage protection controllers protect low-voltage systems against highvoltage faults of up to +28V when used with a -30V pFET. When the input voltage exceeds the OVLO threshold, these devices turn off the external pFET to prevent damage to protected components.

The typical overvoltage trip level is set to 7.18V (MAX4923), 6.16V (MAX4924), 5.65V (MAX4925), and 4.46V (MAX4926). When the supply drops below the UVLO threshold, the devices turn off the external pFET.

IN is ESD protected to $\pm 15 kV$ (Human Body Model) when bypassed with a 1 μF ceramic capacitor to ground.

Undervoltage Lockout (UVLO)

The MAX4923–MAX4926 have a fixed 2.44V (typ) UVLO level. When V_{IN} is less than $V_{UVLO},\,GATE$ is high and FLAG is high.

Overvoltage Lockout (OVLO)

The MAX4923 has a 7.18V (typ) OVLO; the MAX4924 has a 6.16V (typ) OVLO; the MAX4925 has a 5.65V (typ) OVLO; and the MAX4926 has a 4.46V (typ) OVLO. When V_{IN} is greater than V_{OVLO} , GATE is high and FLAG is high.

FLAG Output

The open-drain FLAG output is used to signal to the host system that there is a fault with the input voltage. FLAG goes high during an overvoltage or undervoltage fault. Connect a pullup resistor from FLAG to the logic I/O voltage of the host system.

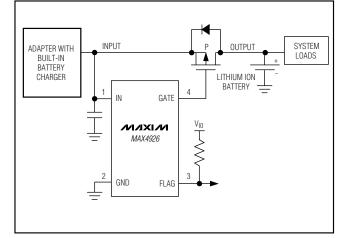


Figure 3. MAX4926 Typical Operating Circuit

Device Operation

The MAX4923–MAX4926 have an on-board state machine to control device operation. A flowchart is shown in Figure 2. At initial power up, if $V_{IN} < V_{UVLO}$ or if $V_{IN} > V_{OVLO}$, both GATE and FLAG are high. When $V_{UVLO} < V_{IN} < V_{OVLO}$, an internal timer starts counting and the device enters its on state after a 20ms delay. At any time if V_{IN} drops below V_{UVLO} or above V_{OVLO} , both GATE and FLAG transition high.

Application Information

MAX4926 Application

In a typical application for the MAX4926, an external adapter with built-in battery charger is connected to IN and a battery is connected to the drain of the external FET. When the adapter is unplugged, IN is directly connected to the battery through the external FET. Since the battery voltage is typically greater than V_{UVLO} , the GATE voltage stays low and the device remains powered by the battery.

MOSFET Selection

The MAX4923–MAX4926 are designed for use with either a single pFET or dual pFETs in parallel. MOSFETs with $R_{DS(ON)}$ specified for a V_{GS} of -4.5V are recommended. For input supplies near the UVLO maximum of 2.5V, use a MOSFET specified for a lower V_{GS} voltage. Also, the V_{DS} must be -30V and the V_{GS} (max) must be higher than the VOVLO (max) for the MOSFET to withstand the full +28V input range of the MAX4923–MAX4926.

MAX4923-MAX4926

Table 1. MOSFETS Suggestions

PART	CONFIGURATON/ PACKAGE	V _{DS} MAX (V)	R _{ON} MAX (mΩ) at V _{GS} = -4.5V	MANUFACTURER	
Si3993DV	Dual/TSOP-6	-30	245 each		
Si1433DH	Single/SOT-363	-30	260		
Si3983DV	Dual/TSOP-6	-20	110 each	Vishay Siliconix	
Si1413DH	Single/SOT-363	-20	115	www.vishay.com	
Si5933DC	Dual/1206-8	-20	110 each		
Si6991DQ	Dual/TSSOP-8	-30	68 each		

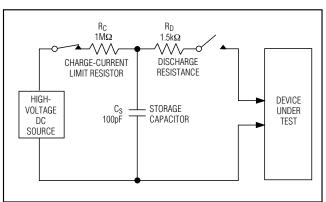


Figure 4. Human Body ESD Test Model

IN Bypass Consideration

For most applications, bypass IN to GND with a 1μ F ceramic capacitor. If the power source has significant inductance due to long lead length, take care to prevent overshoots due to the LC tank circuit and provide protection if necessary to prevent exceeding the 30V absolute maximum rating on IN.

ESD Test Conditions

The MAX4923–MAX4926 are ESD protected to ± 15 kV (typ) Human Body Model on IN when IN is bypassed to ground with a 1µF ceramic capacitor as close as possible to IN.

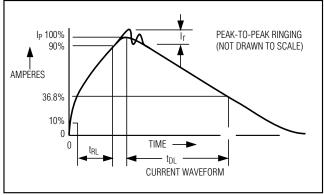


Figure 5. Human Body Model Current Waveform

Human Body Model

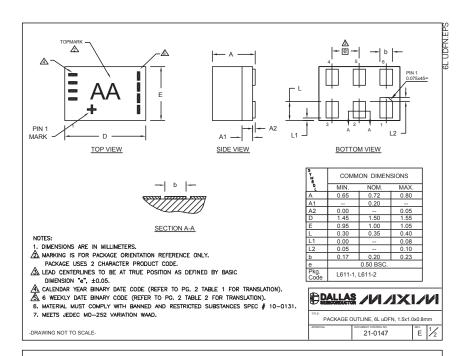
Figure 4 shows the Human Body Model and Figure 5 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest that is then discharged into the device through a $1.5k\Omega$ resistor.

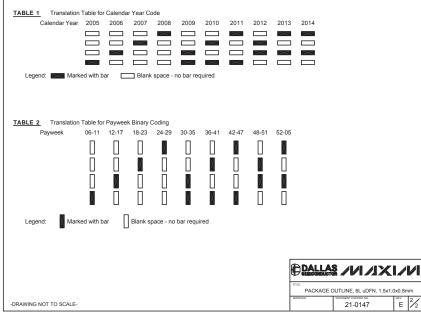
_____Chip Information

MAX4923-MAX4926

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <u>www.maxim-ic.com/packages</u>.)





Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 408-737-7600

is a registered trademark of Maxim Integrated Products, Inc.